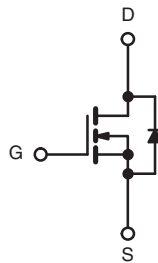
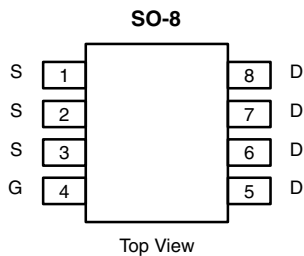


AO4294-VB Datasheet

N-Channel 100-V (D-S) Super Trench Power MOSFET

| PRODUCT SUMMARY | | | |
|-----------------|--------------------------------|------------------------|--------------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) Max. | I_D (A) ^a | Q_g (Typ.) |
| 100 | 0.0082 at $V_{GS} = 10$ V | 15.5 | 27.9 nC |
| | 0.0095 at $V_{GS} = 7.5$ V | 14.8 | |
| | 0.0105 at $V_{GS} = 6.0$ V | 14.0 | |



N-Channel MOSFET

FEATURES

- Super Trench technology Power MOSFET
- Excellent gate charge x Rds (on) product(FOM)
- Very low on-resistance Rds (on)
- 100 % R_g and UIS Tested



RoHS
 COMPLIANT
 HALOGEN
FREE

APPLICATIONS

- DC/DC Primary Side Switch
- Telecom/Server
- Motor Drive Control
- Synchronous Rectification

| ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted) | | | |
|---|----------------|----------------------|------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | |
| Continuous Drain Current ($T_J = 150$ °C) | $T_C = 25$ °C | 15.5 | A |
| | $T_C = 70$ °C | 13 | |
| | $T_A = 25$ °C | 10.2 ^{b, c} | |
| | $T_A = 70$ °C | 7.4 ^{b, c} | |
| Pulsed Drain Current ($t = 300$ μ s) | I_{DM} | 70 | |
| Continuous Source-Drain Diode Current | $T_C = 25$ °C | 7 | |
| | $T_A = 25$ °C | 3.1 ^{b, c} | |
| Single Pulse Avalanche Current | I_{AS} | 30 | |
| Avalanche Energy | E_{AS} | 45 | mJ |
| Maximum Power Dissipation | $T_C = 25$ °C | 7.8 | W |
| | $T_C = 70$ °C | 5 | |
| | $T_A = 25$ °C | 3.5 ^{b, c} | |
| | $T_A = 70$ °C | 2.2 ^{b, c} | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Typical | Maximum | Unit |
|---|------------|---------|---------|------|
| Maximum Junction-to-Ambient ^{b, d} | R_{thJA} | 29 | 35 | °C/W |
| Maximum Junction-to-Foot (Drain) | R_{thJF} | 13 | 16 | |

Notes:

- Based on $T_C = 25$ °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 10$ s.
- Maximum under steady state conditions is 80 °C/W.

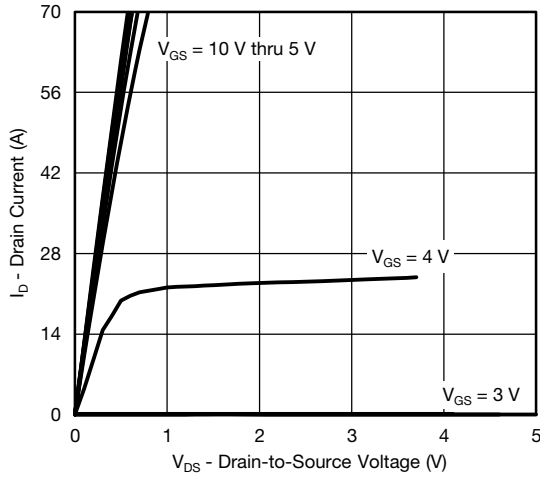
| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | |
|--|-------------------------|--|------|--------|-----------|----------------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | 100 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = 250\text{ }\mu\text{A}$ | | 67 | | mV/ $^\circ\text{C}$ |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | -6.4 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2 | | 3.3 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}$ | | | 1 | μA |
| | | $V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq 5\text{ V}, V_{GS} = 10\text{ V}$ | 30 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}, I_D = 15\text{ A}$ | | 0.0082 | | Ω |
| | | $V_{GS} = 7.5\text{ V}, I_D = 12\text{ A}$ | | 0.0095 | | |
| | | $V_{GS} = 6.0\text{ V}, I_D = 10\text{ A}$ | | 0.0105 | | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = 15\text{ V}, I_D = 15\text{ A}$ | | 54 | | S |
| Dynamic^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 3410 | | pF |
| Output Capacitance | C_{oss} | | | 790 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 160 | | |
| Total Gate Charge | Q_g | $V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 10\text{ A}$ | | 45.6 | 69 | nC |
| | | $V_{DS} = 50\text{ V}, V_{GS} = 6\text{ V}, I_D = 10\text{ A}$ | | 27.9 | 42 | |
| Gate-Source Charge | Q_{gs} | | | 8.5 | | |
| Gate-Drain Charge | Q_{gd} | | | 9.2 | | |
| Output Charge | Q_{oss} | $V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$ | | 63 | 95 | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | 0.4 | 1.3 | 2.6 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 50\text{ V}, R_L = 5\text{ }\Omega$ $I_D \equiv 10\text{ A}, V_{GEN} = 7.5\text{ V}, R_g = 1\text{ }\Omega$ | | 16 | 32 | ns |
| Rise Time | t_r | | | 11 | 22 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 35 | 70 | |
| Fall Time | t_f | | | 10 | 20 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 50\text{ V}, R_L = 5\text{ }\Omega$ $I_D \equiv 10\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$ | | 14 | 28 | |
| Rise Time | t_r | | | 10 | 20 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 36 | 70 | |
| Fall Time | t_f | | | 10 | 20 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^\circ\text{C}$ | | | 7 | A |
| Pulse Diode Forward Current ^a | I_{SM} | | | | 70 | |
| Body Diode Voltage | V_{SD} | $I_S = 5\text{ A}$ | | 0.75 | 1.1 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 10\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$ | | 49 | 95 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 58 | 115 | nC |
| Reverse Recovery Fall Time | t_a | | | 21 | | ns |
| Reverse Recovery Rise Time | t_b | | | 28 | | |

Notes:

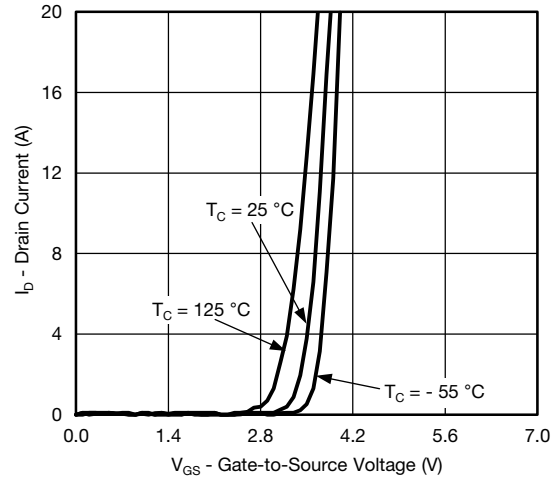
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

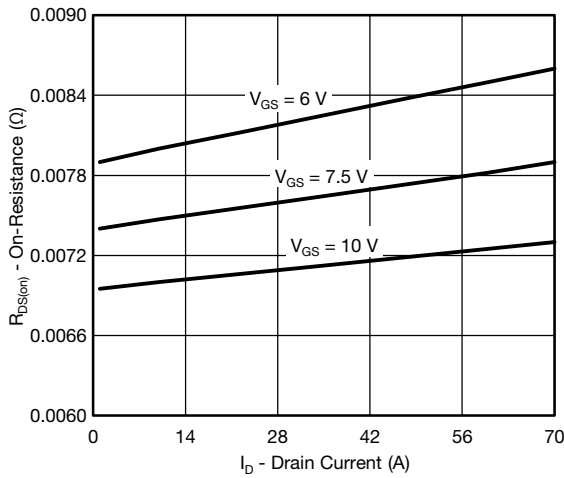
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



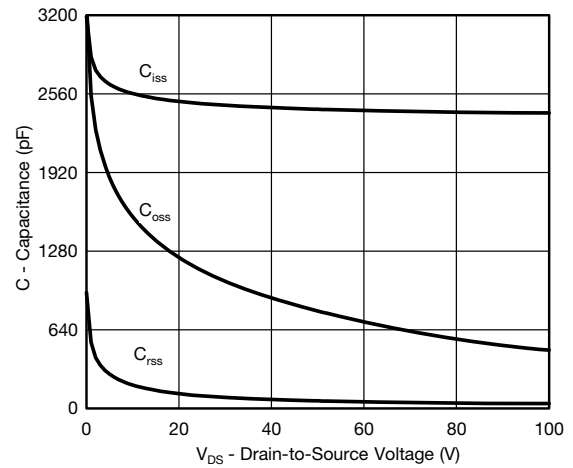
Output Characteristics



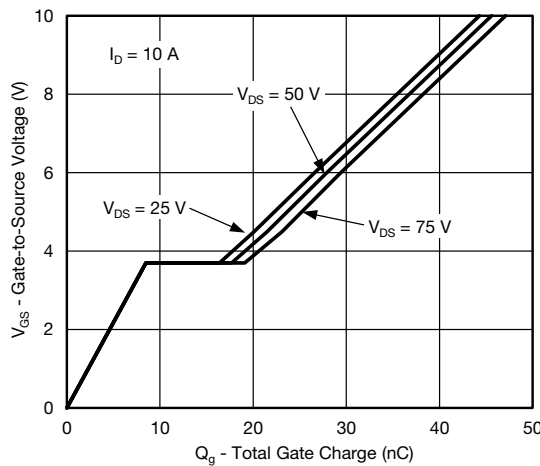
Transfer Characteristics



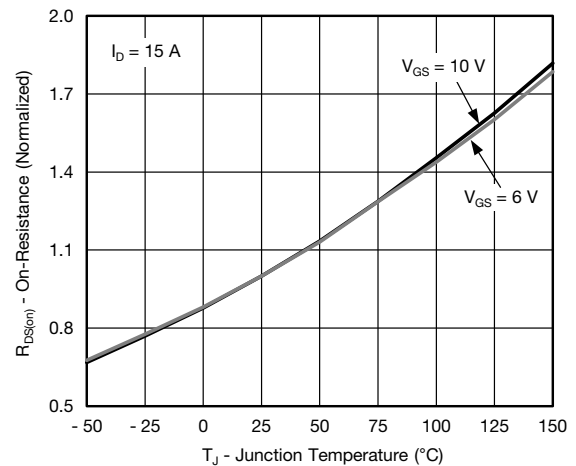
On-Resistance vs. Drain Current



Capacitance

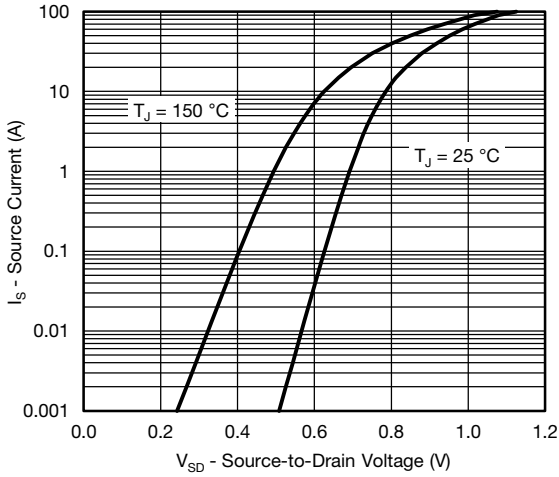


Gate Charge

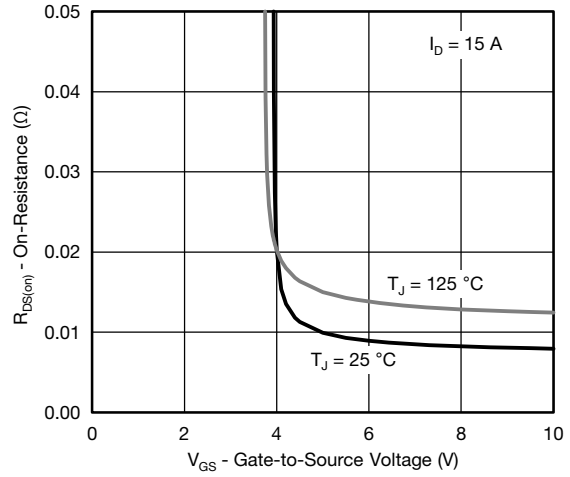


On-Resistance vs. Junction Temperature

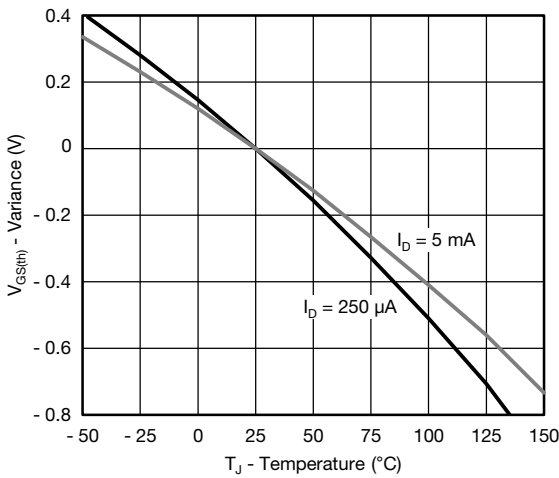
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



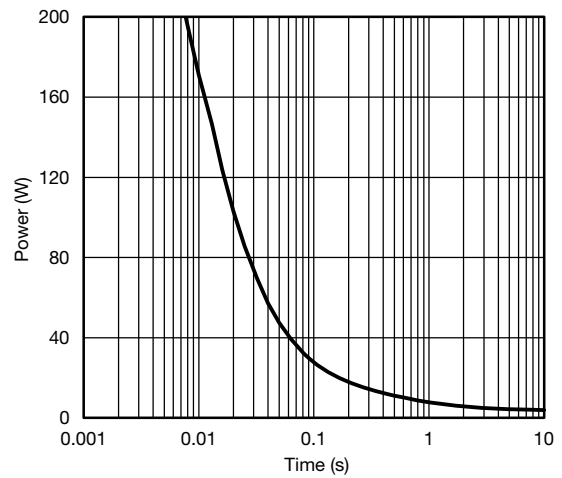
Source-Drain Diode Forward Voltage



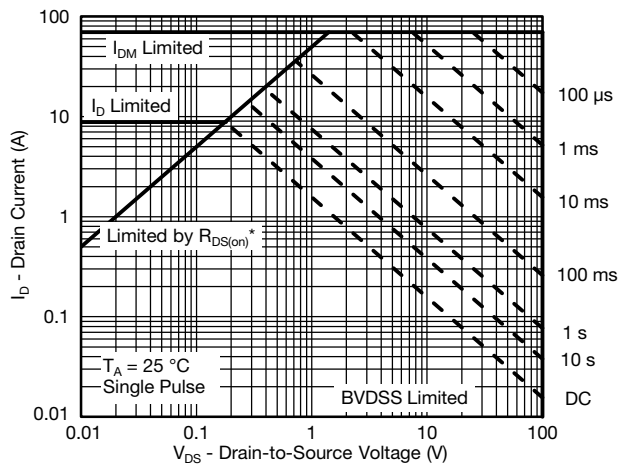
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



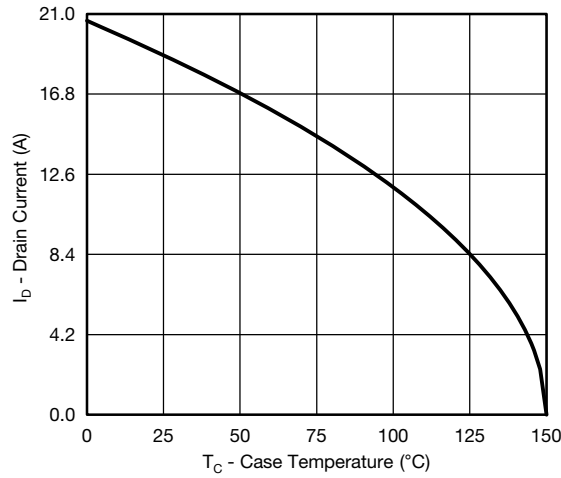
Single Pulse Power, Junction-to-Ambient



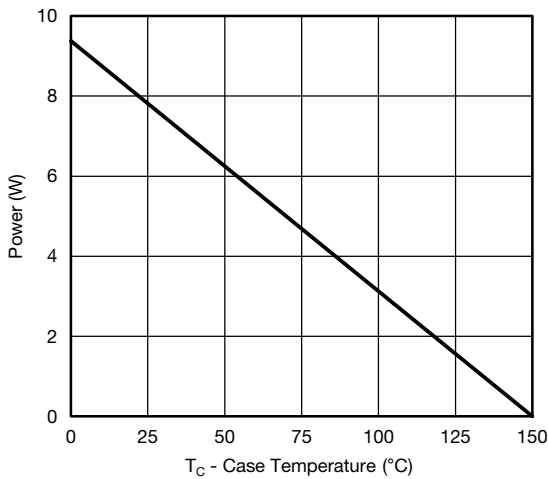
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

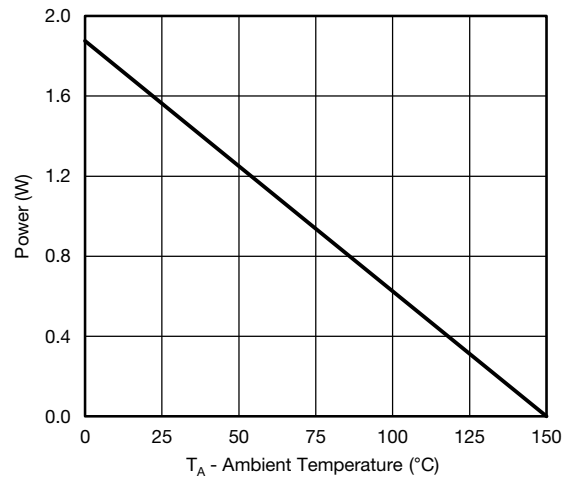
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*



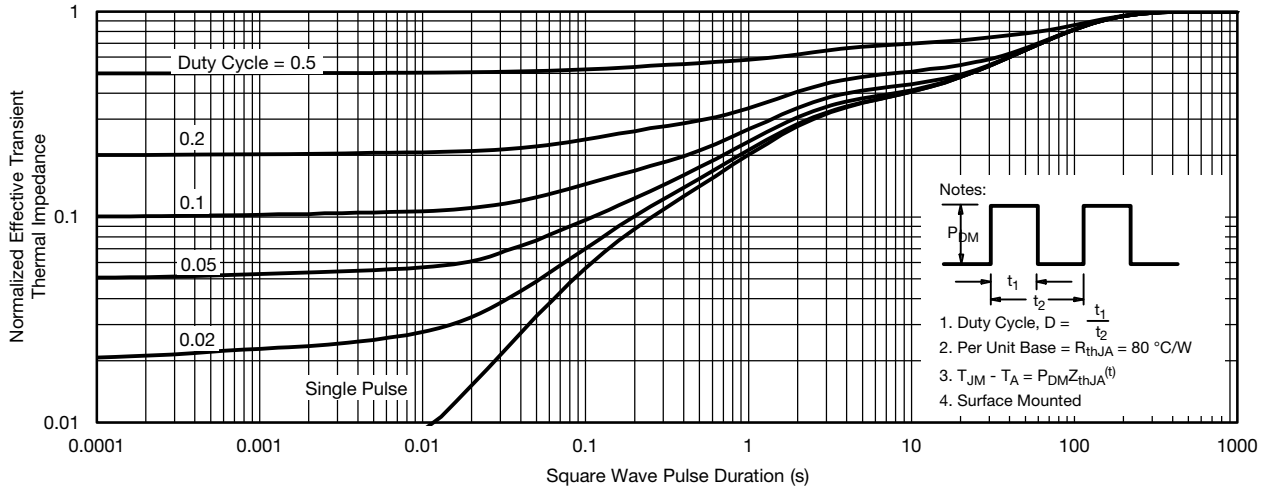
Power, Junction-to-Foot



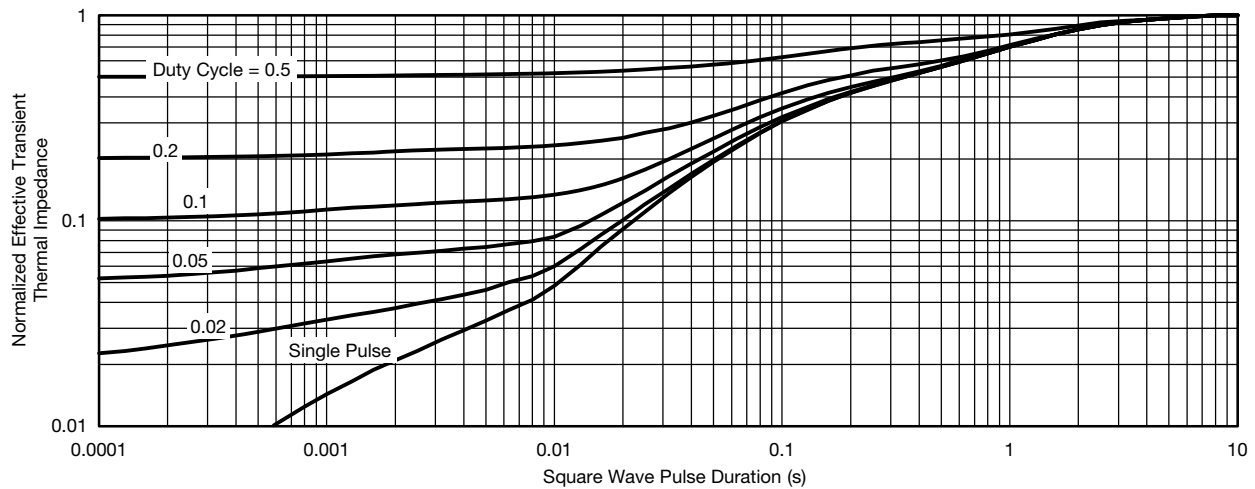
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

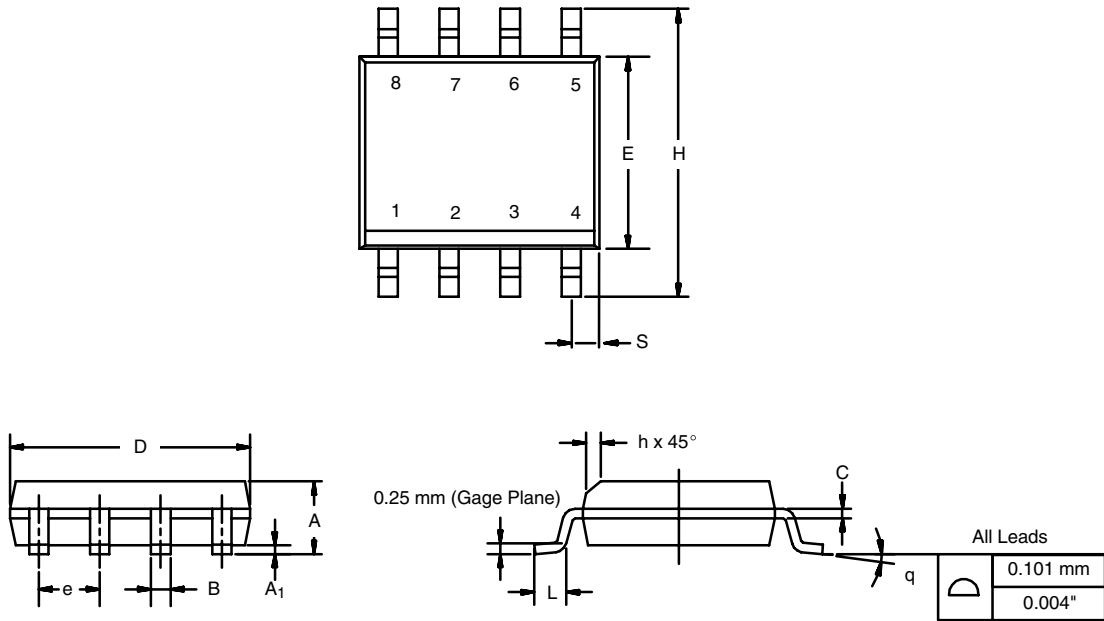


Normalized Thermal Transient Impedance, Junction-to-Ambient



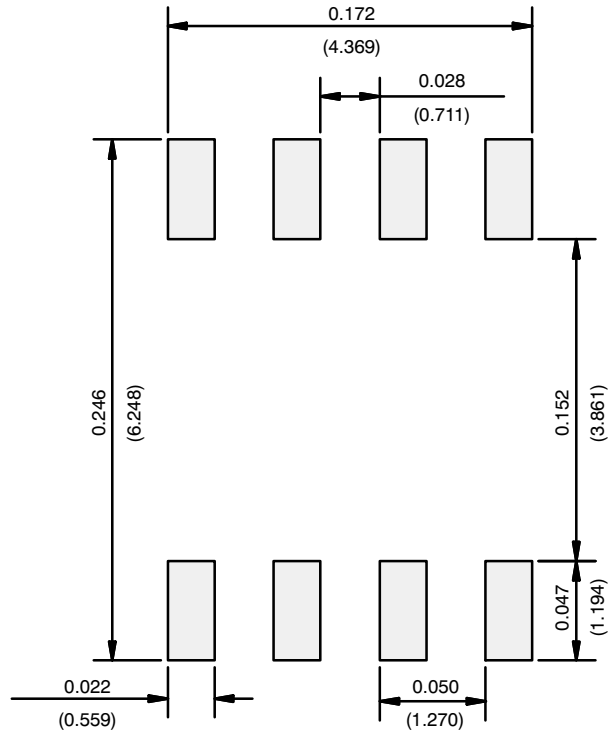
Normalized Thermal Transient Impedance, Junction-to-Foot

SOIC (NARROW): 8-LEAD
JEDEC Part Number: MS-012



| DIM | MILLIMETERS | | INCHES | |
|--------------------------------|-------------|------|-----------|-------|
| | Min | Max | Min | Max |
| A | 1.35 | 1.75 | 0.053 | 0.069 |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 |
| B | 0.35 | 0.51 | 0.014 | 0.020 |
| C | 0.19 | 0.25 | 0.0075 | 0.010 |
| D | 4.80 | 5.00 | 0.189 | 0.196 |
| E | 3.80 | 4.00 | 0.150 | 0.157 |
| e | 1.27 BSC | | 0.050 BSC | |
| H | 5.80 | 6.20 | 0.228 | 0.244 |
| h | 0.25 | 0.50 | 0.010 | 0.020 |
| L | 0.50 | 0.93 | 0.020 | 0.037 |
| q | 0° | 8° | 0° | 8° |
| S | 0.44 | 0.64 | 0.018 | 0.026 |
| ECN: C-06527-Rev. I, 11-Sep-06 | | | | |
| DWG: 5498 | | | | |

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads
Dimensions in Inches/(mm)

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